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FQD1N60C / FQU1N60C

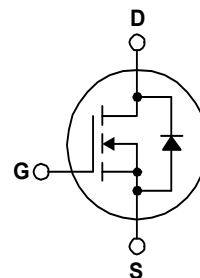
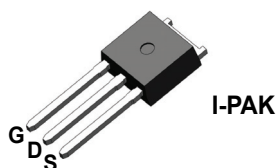
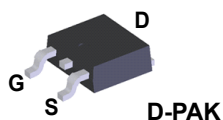
N-Channel QFET® MOSFET 600 V, 1.0 A, 11.5 Ω

Features

- 1 A, 600 V, $R_{DS(on)} = 11.5 \Omega$ (Max.) @ $V_{GS} = 10$ V, $I_D = 0.5$ A
- Low Gate Charge (Typ. 4.8 nC)
- Low C_{rss} (Typ. 3.5 pF)
- 100% Avalanche Tested
- RoHS Compliant

Description

This N-Channel enhancement mode power MOSFET is produced using ON Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FQD1N60CTM / FQU1N60CTU	Unit
V_{DSS}	Drain-Source Voltage	600	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$)	1	A
	- Continuous ($T_C = 100^\circ\text{C}$)	0.6	A
I_{DM}	Drain Current - Pulsed (Note 1)	4	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	33	mJ
I_{AR}	Avalanche Current (Note 1)	1	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	2.8	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
P_D	Power Dissipation ($T_A = 25^\circ\text{C}$)*	2.5	W
	Power Dissipation ($T_C = 25^\circ\text{C}$)	28	W
	- Derate Above 25°C	0.22	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	FQD1N60CTM / FQU1N60CTU	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	4.53	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Minimum Pad of 2-oz Copper), Max.	110	
	Thermal Resistance, Junction-to-Ambient (*1 in ² Pad of 2-oz Copper), Max.	50	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQD1N60CTM	FQD1N60C	D-PAK	Tape and Reel	330 mm	16mm	2500 units
FQU1N60CTU	FQU1N60C	I-PAK	Tube	N/A	N/A	70 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	600	--	--	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	--	0.6	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 600 V, V _{GS} = 0 V	--	--	1	μA
		V _{DS} = 480 V, T _C = 125°C	--	--	10	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	2.0	--	4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 0.5 A	--	9.3	11.5	Ω
g _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 0.5 A	--	0.75	--	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz	--	130	170	pF
C _{oss}	Output Capacitance		--	19	25	pF
C _{rss}	Reverse Transfer Capacitance		--	3.5	4.5	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 300 V, I _D = 1.1 A, R _G = 25 Ω	--	7	24	ns
t _r	Turn-On Rise Time		--	21	52	ns
t _{d(off)}	Turn-Off Delay Time		--	13	36	ns
t _f	Turn-Off Fall Time		--	27	64	ns
Q _g	Total Gate Charge	V _{DS} = 480 V, I _D = 1.1 A, V _{GS} = 10 V	--	4.8	6.2	nC
Q _{gs}	Gate-Source Charge		--	0.7	--	nC
Q _{gd}	Gate-Drain Charge		--	2.7	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	1	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	4	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 0.5 A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 1.1 A,	--	190	--	ns
Q _{rr}	Reverse Recovery Charge	di _F / dt = 100 A/μs	--	0.53	--	μC

Notes:

1. Repetitive Rating : pulse-width limited by maximum junction temperature.
2. $L = 59\text{ mH}, I_{AS} = 1.1\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\text{ }\Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 1.1\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature.

Typical Characteristics

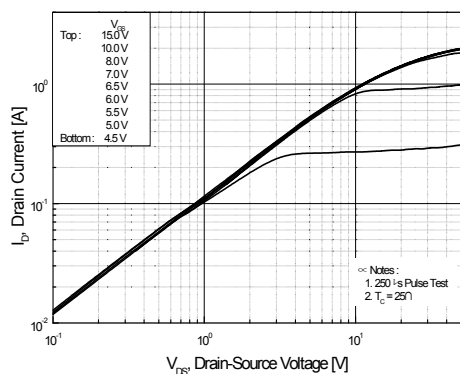


Figure 1. On-Region Characteristics

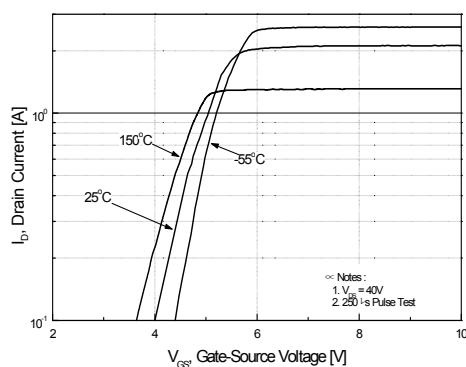


Figure 2. Transfer Characteristics

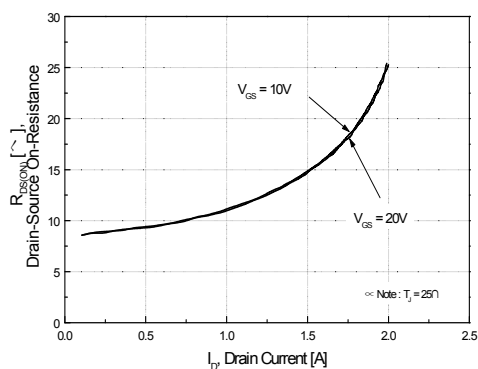


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

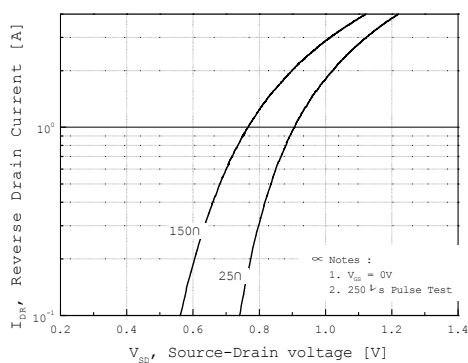


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

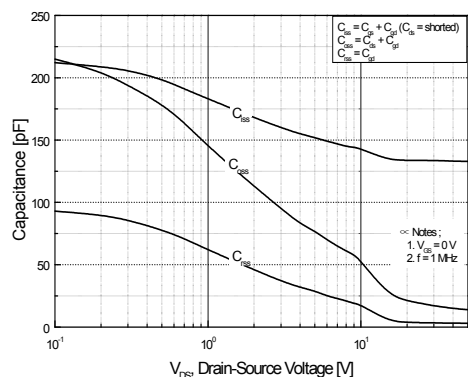


Figure 5. Capacitance Characteristics

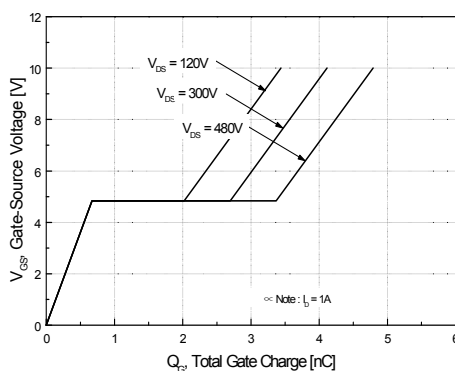


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

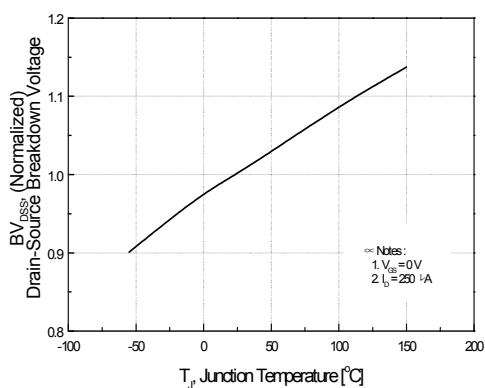


Figure 7. Breakdown Voltage Variation vs Temperature

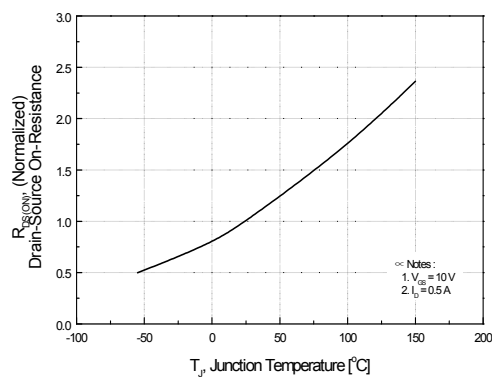


Figure 8. On-Resistance Variation vs Temperature

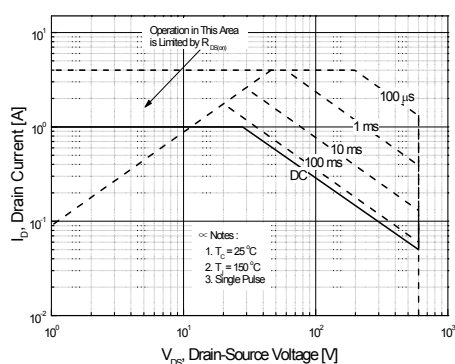


Figure 9. Maximum Safe Operating Area

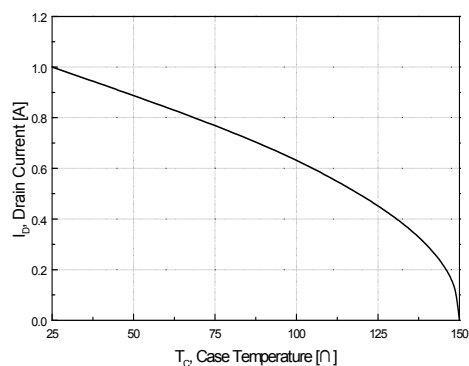


Figure 10. Maximum Drain Current vs Case Temperature

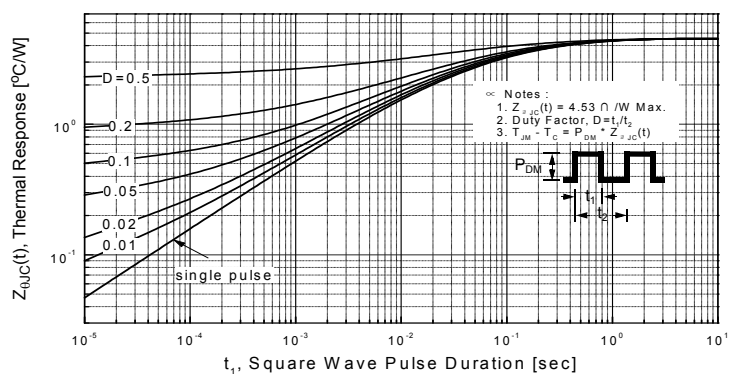


Figure 11. Transient Thermal Response Curve

Figure 12. Gate Charge Test Circuit & Waveform

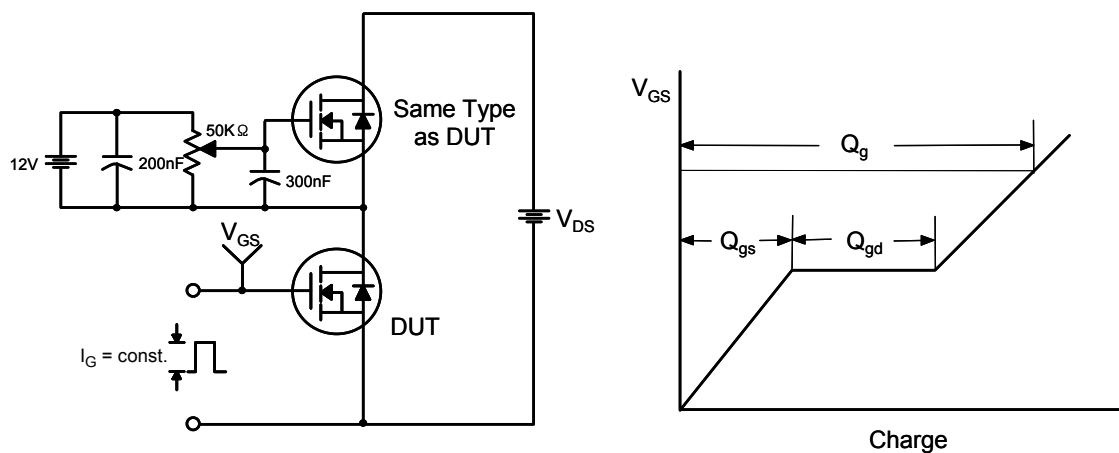


Figure 13. Resistive Switching Test Circuit & Waveforms

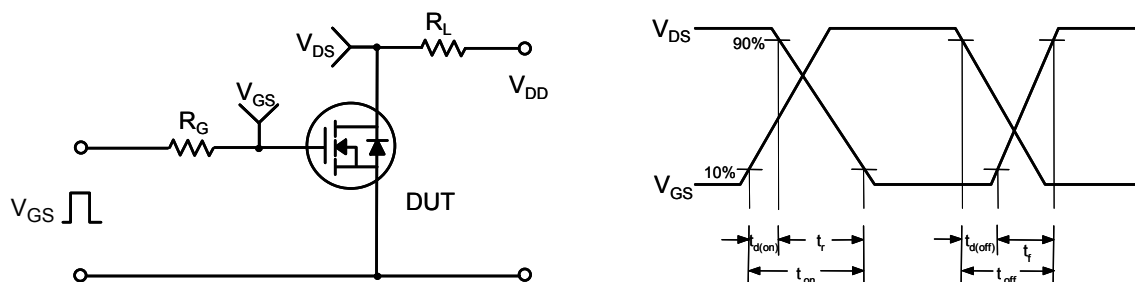
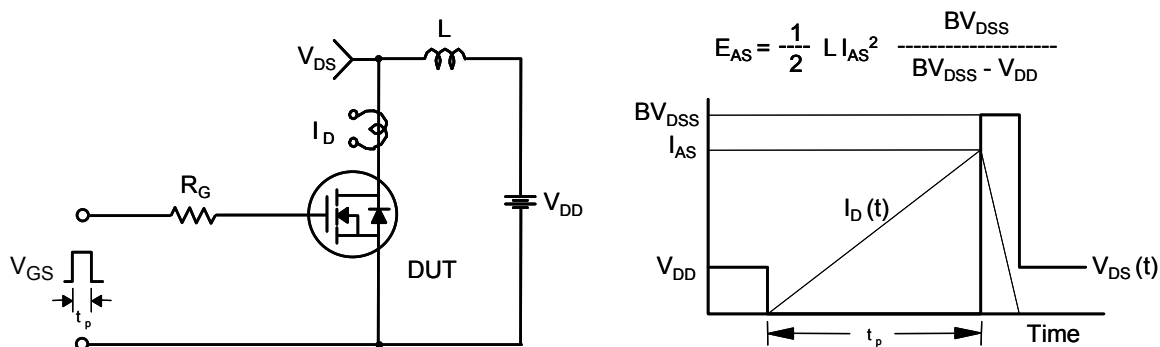
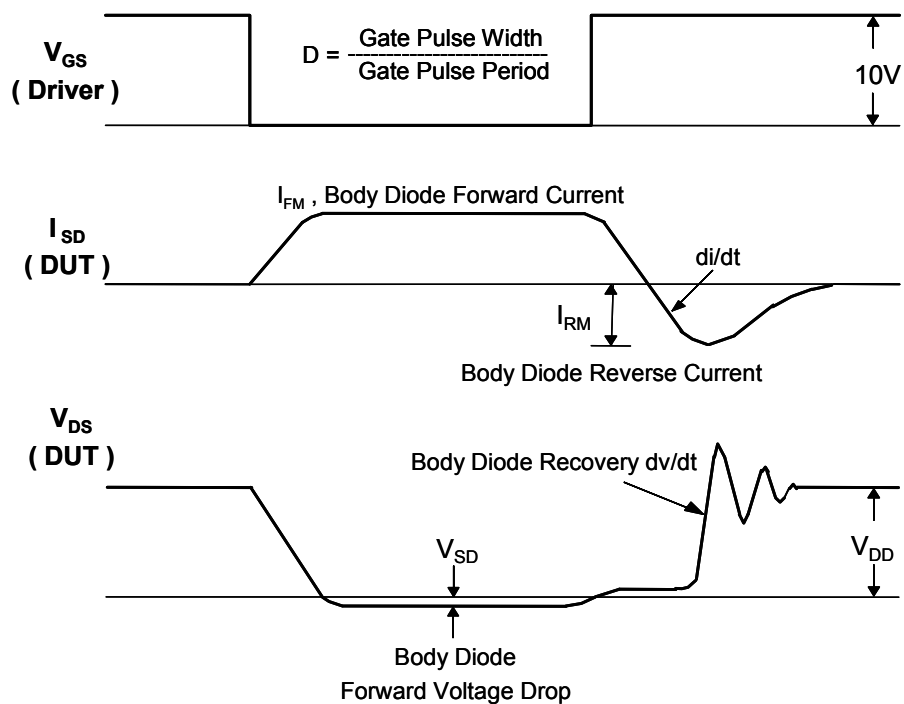
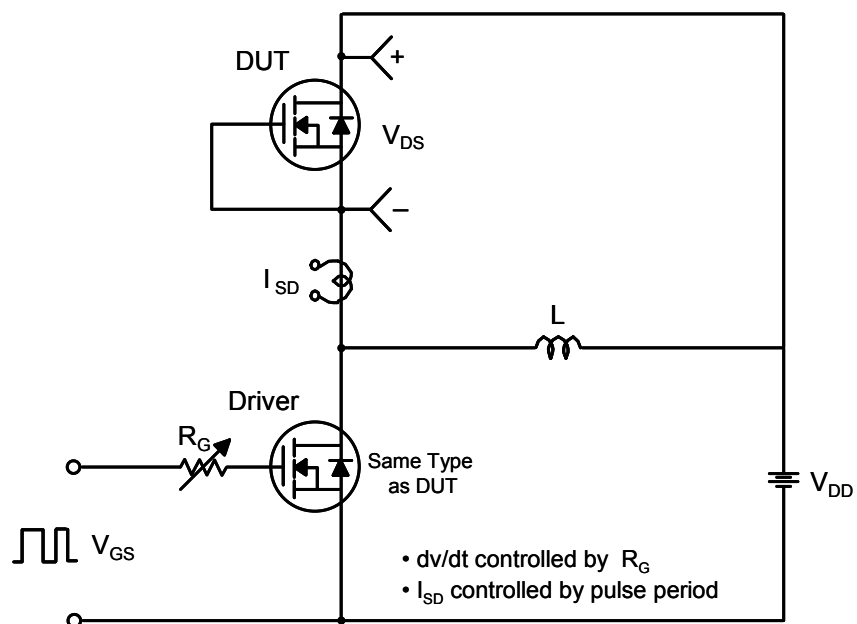


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms





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